

SANYO Semiconductors DATA SHEET

An ON Semiconductor Company

2SB1123 / 2SD1623 -

PNP / NPN Epitaxial Planar Silicon Transistors

High-Current Switching Applications

Applications

· Voltage regulators, relay drivers, lamp drivers, electrical equipment.

Features

- · Adoption of FBET, MBIT processes.
- · Low collector-to-emitter saturation voltage.
- · Large current capacity and wide ASO.
- · Fast switching speed.
- The ultraminiature package facilitates higher-density mounting, thus allows the applied hybrid IC's further miniaturization.

Specifications (): 2SB1123

Absolute Maximum Ratings at Ta=25°C

Parameter	Symbol	Conditions	Ratings	Unit
Collector-to-Base Voltage	VCBO		(-)60	V
Collector-to-Emitter Voltage	VCEO		(-)50	V
Emitter-to-Base Voltage	VEBO		(-)6	V
Collector Current	IC		(-)2	А
Collector Current (Pulse)	ICP		(-)4	А
Collector Dissipation	PC		0.5	W
	PC	Mounted on a ceramic board (250mm ² ×0.8mm)	1.3	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

Marking 2SB1123 : BF 2SD1623 : DF

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Electrical Characteristics at Ta=25°C

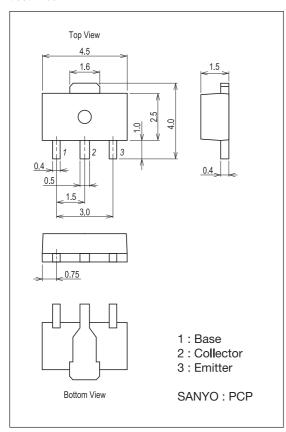
Parameter	Symbol	Conditions	Ratings			1.1
			min	typ	max	Unit
Collector Cutoff Current	ICBO	V _{CB} =(-)50V, I _E =0A			(-)100	nA
Emitter Cutoff Current	IEBO	V _{EB} =(-)4V, I _C =0A			(-)100	nA
DC Current Gain	hFE1	VCE=(-)2V, IC=(-)100mA	100*		560*	
	hFE2	V _{CE} =(-)2V, I _C =(-)1.5A	40			
Gain-Bandwidth Product	f⊤	V _{CE} =(-)10V, I _C =(-)50mA		150		MHz
Output Capacitance	Cob	V _{CB} =(-)10V, f=1MHz		(22)12		pF
Collector-to-Emitter Saturation Voltage	V _{CE} (sat)	I _C =(-)1A, I _B =(-)50mA		(-0.3)0.15	(-0.7)0.4	V
Base-to-Emitter Saturation Voltage	V _{BE} (sat)	I _C =(-)1A, I _B =(-)50mA		(-)0.9	(-)1.2	V
Collector-to-Base Breakdown Voltage	V(BR)CBO	I _C =(-)10μA, I _E =0A	(-)60			V
Collector-to-Emitter Breakdown Voltage	V(BR)CEO	I _C =(-)1mA, R _{BE} =∞	(-)50			V
Emitter-to-Base Breakdown Voltage	V(BR)EBO	I _E =(-)10μA, I _C =0A	(-)6			V
Turn-ON Time	ton	See specified Test Circuit.		(60)60		ns
Storage Time	t _{stg}	See specified Test Circuit.		(450)550		ns
Fall Time	tf	See specified Test Circuit.		(30)30		ns

^{*:} The 2SB1123 / 2SD1623 are classified by 100mA hFE as follows:

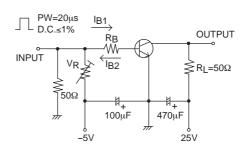
Rank	R	S	T	U
$h_{ ext{FE}}$	100 to 200	140 to 280	200 to 400	280 to 560

Package Dimensions

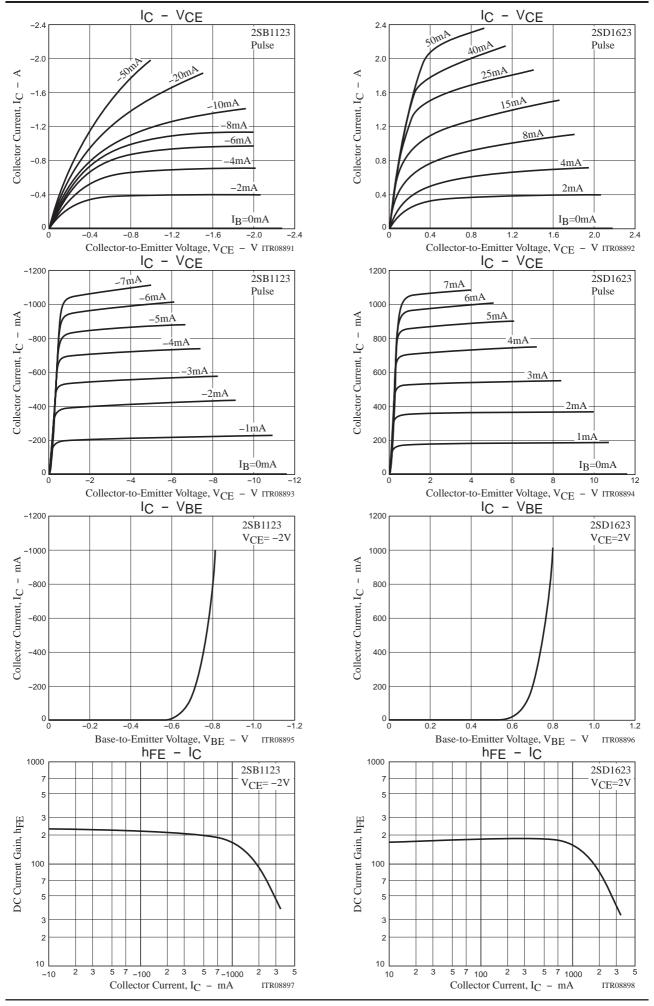
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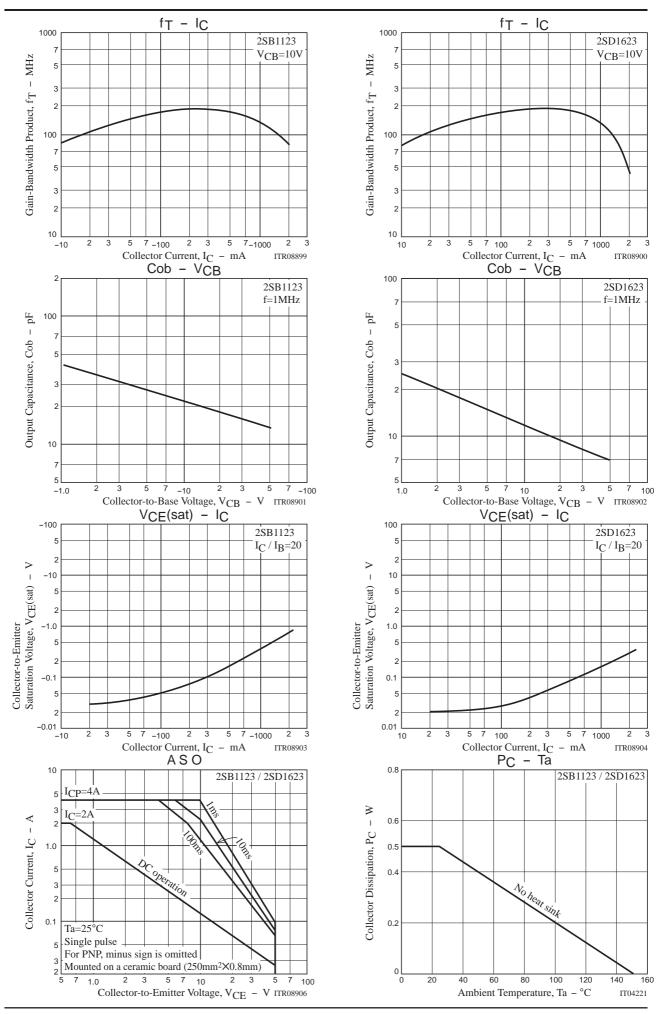


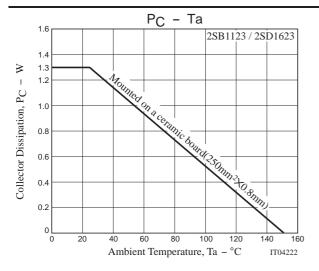
Switching Time Test Circuit



IC=10IB1=-10IB2=500mA (For PNP, the polarity is reversed)







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